Fig. 1

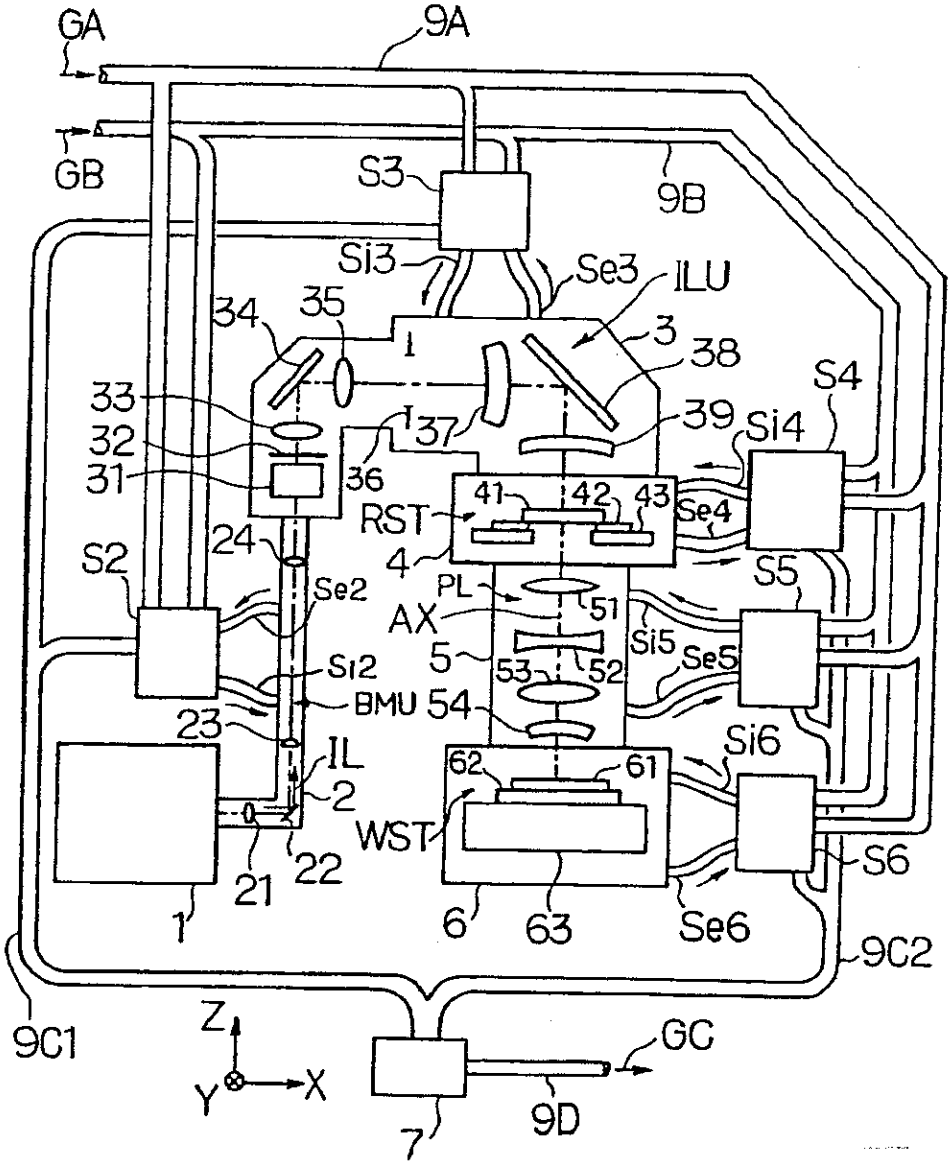

GA
9A
GB
S3
9B
Si3
Se3
ILU
34
35
1
3
38
S4
33
37
39
Si4
32
31
36
41
42
43
RST
Se4
24
S2
4
S5
Se2
PL
51
AX
Si5
Se5
5
53
52
Si2
BMU
54
23
IL
Si6
62
61
2
WST
S6
21
22
1
6
63
Se6
9C2
9C1
Z
Y
X
GC
7
9D

Fig. 2

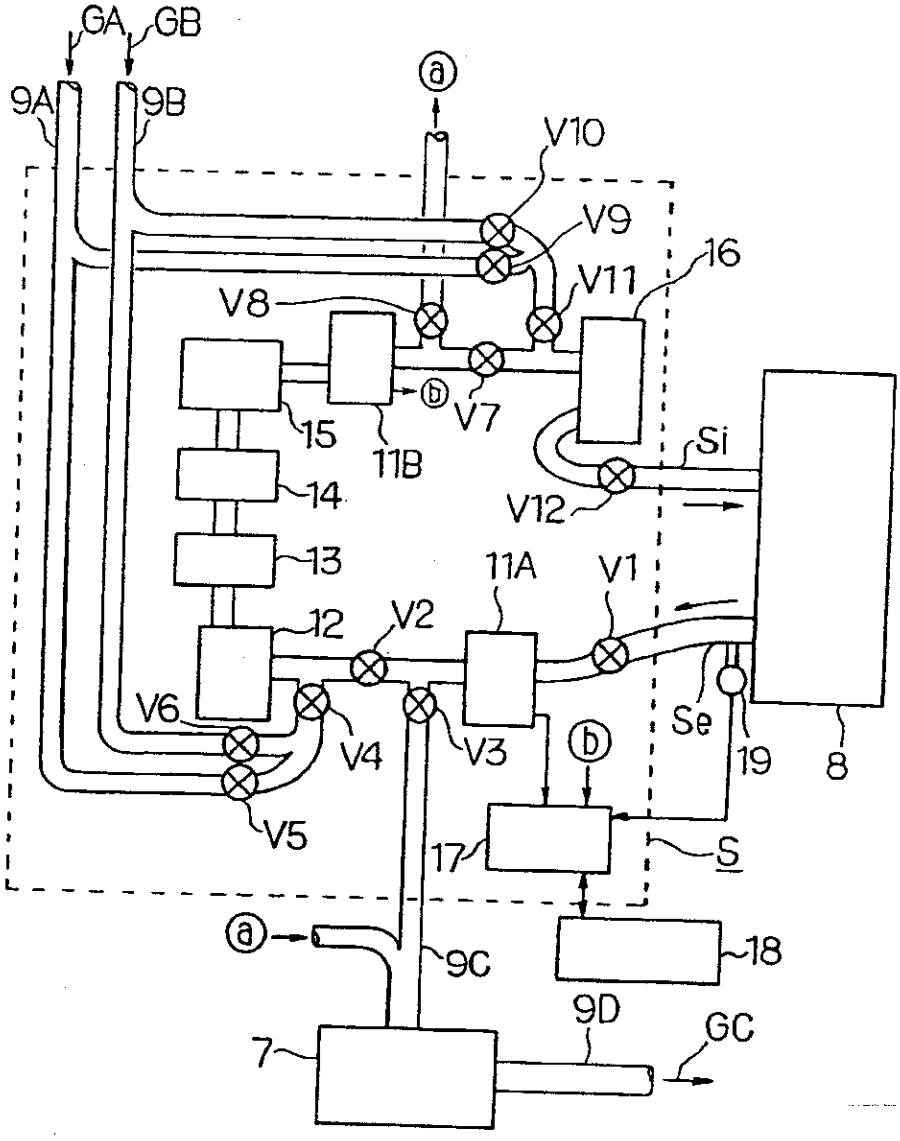

GA
GB
9A
9B
ⓐ
V10
V9
V11
16
V8
ⓑ
V7
15
11B
14
13
12
V2
11A
V1
Si
V12
V6
V4
V3
Se
19
8
V5
17
S
ⓐ
9C
18
9D
7
GC

Fig. 3

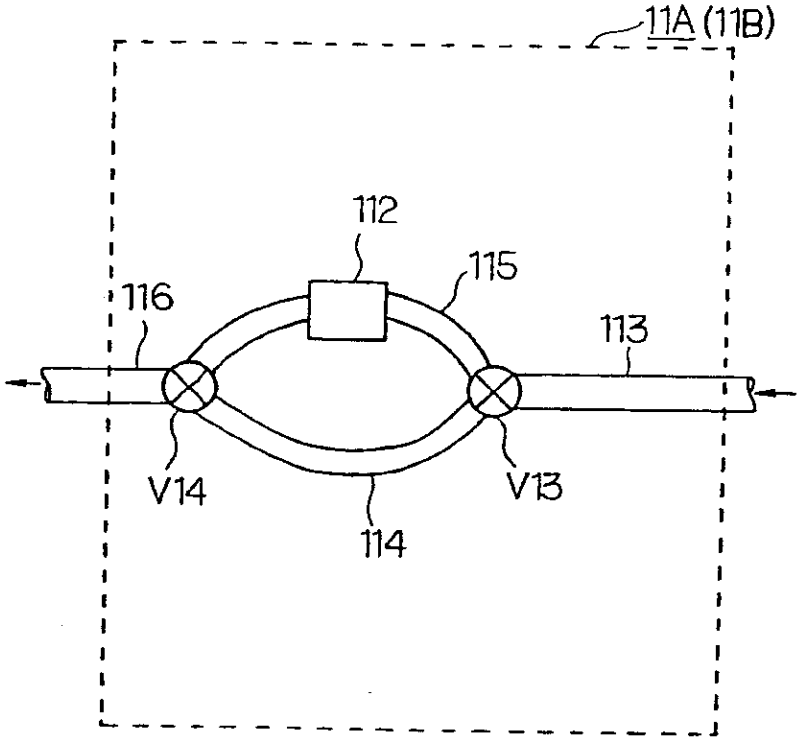

11A (11B)
112
115
116
113
V14
V13
114

Fig. 4

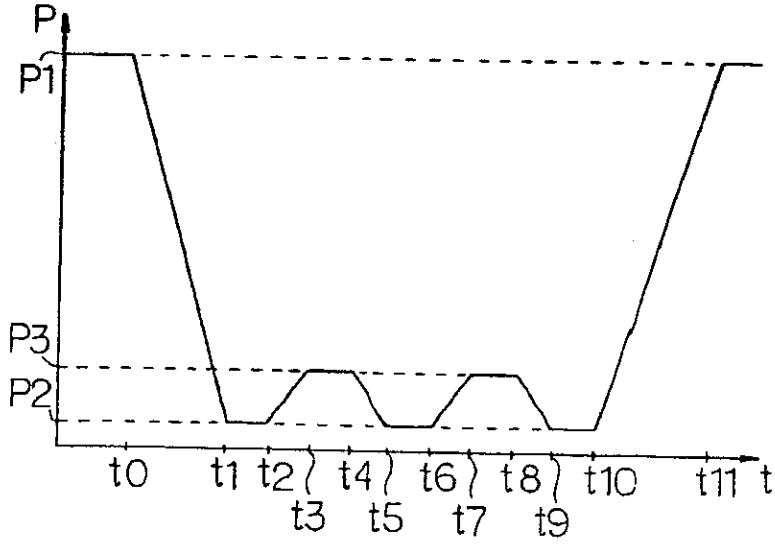
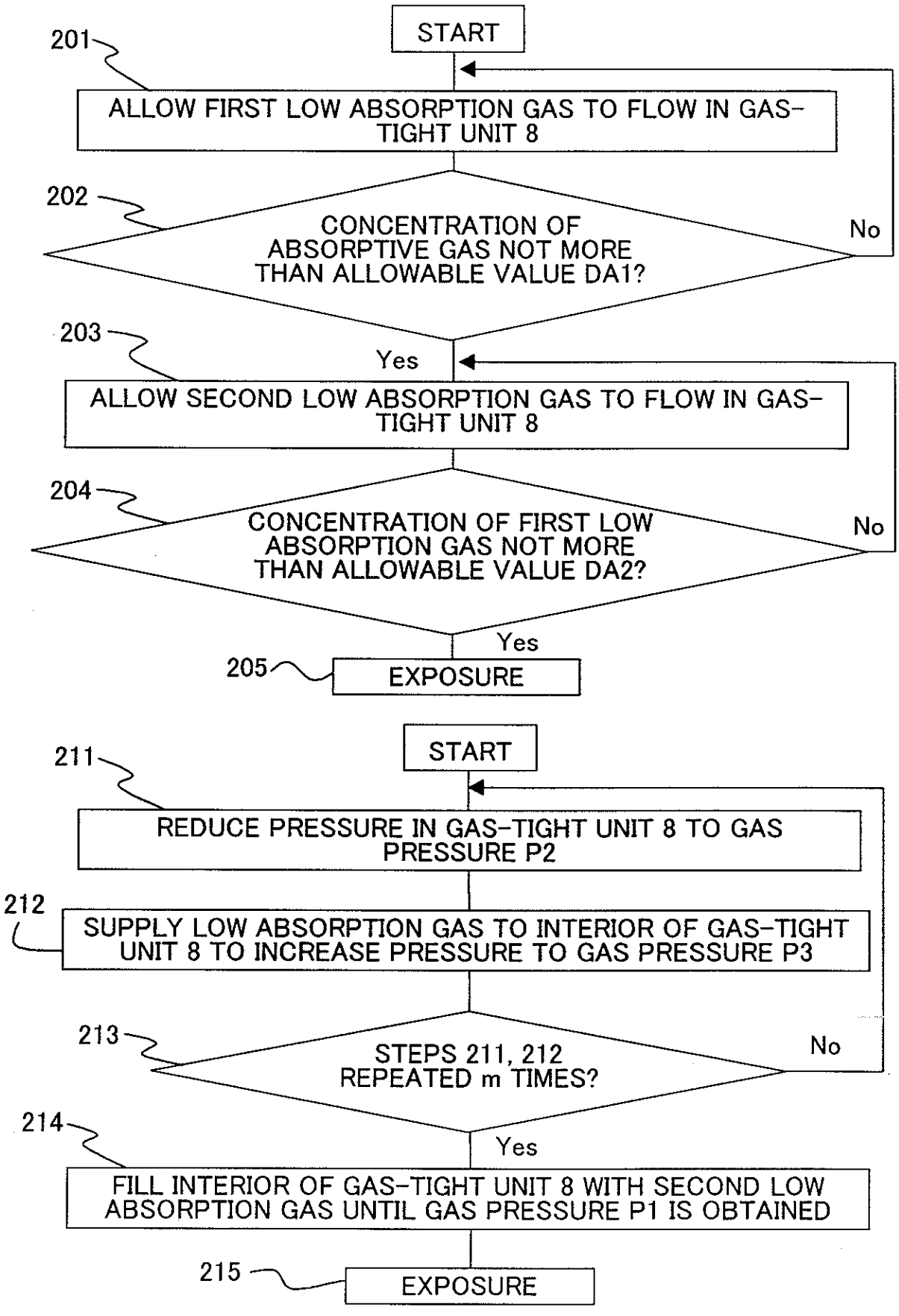

P
P1
P3
P2
t0
t1
t2
t3
t4
t5
t6
t7
t8
t9
t10
t11
t

Fig. 5


START
201
ALLOW FIRST LOW ABSORPTION GAS TO FLOW IN GAS-TIGHT UNIT 8
202
CONCENTRATION OF ABSORPTIVE GAS NOT MORE THAN ALLOWABLE VALUE DA1?
No
Yes
203
ALLOW SECOND LOW ABSORPTION GAS TO FLOW IN GAS-TIGHT UNIT 8
204
CONCENTRATION OF FIRST LOW ABSORPTION GAS NOT MORE THAN ALLOWABLE VALUE DA2?
No
Yes
205
EXPOSURE
START
211
REDUCE PRESSURE IN GAS-TIGHT UNIT 8 TO GAS PRESSURE P2
212
SUPPLY LOW ABSORPTION GAS TO INTERIOR OF GAS-TIGHT UNIT 8 TO INCREASE PRESSURE TO GAS PRESSURE P3
213
STEPS 211, 212 REPEATED m TIMES?
No
Yes
214
FILL INTERIOR OF GAS-TIGHT UNIT 8 WITH SECOND LOW ABSORPTION GAS UNTIL GAS PRESSURE P1 IS OBTAINED
215
EXPOSURE